



MMBT9014

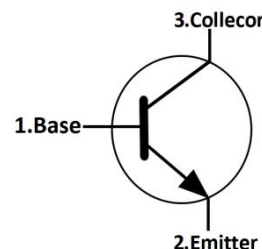
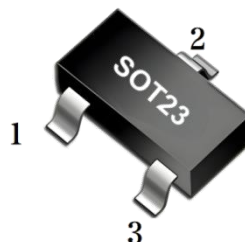
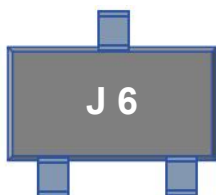
NPN SILICON TRANSISTOR

FEATURES

- *High total power dissipation. (450mW)
- *Excellent hFE linearity.
- *Complementary to MMBT9015.

MARKING

Type Code: Marking: J 6



ABSOLUTE MAXIMUM RATINGS (Tc=25°C, unless otherwise specified)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CB0}	Collector-base voltage	50	V
V _{CEO}	Collector-emitter voltage	45	V
V _{EBO}	Emitter-base voltage	5	V
I _C	Collector current	100	mA
P _C	Collector Power Dissipation	200	mW
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C
ROJA	Thermal Resistance From Junction To Ambient	625	°C/W

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

ELECTRICAL CHARACTERISTICS (Tc=25°C, unless otherwise specified)

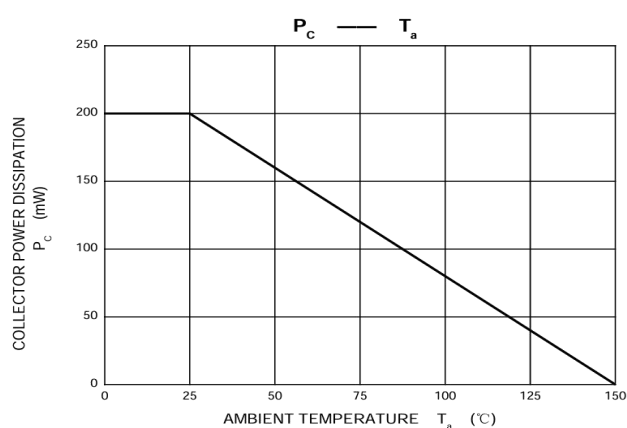
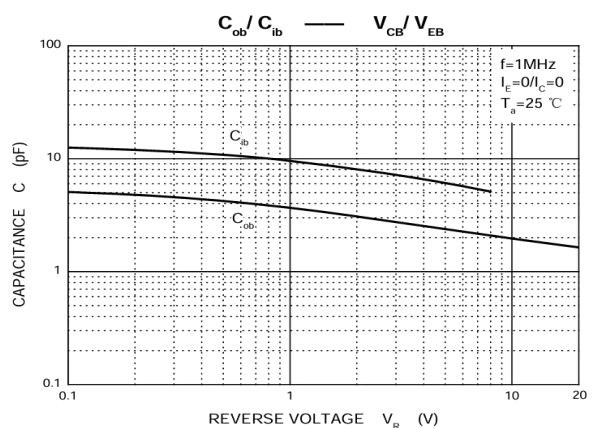
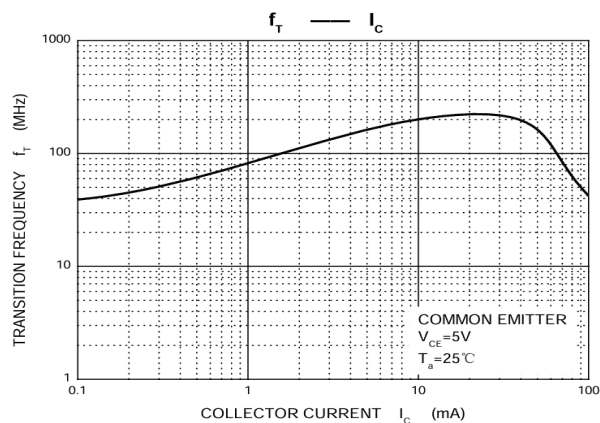
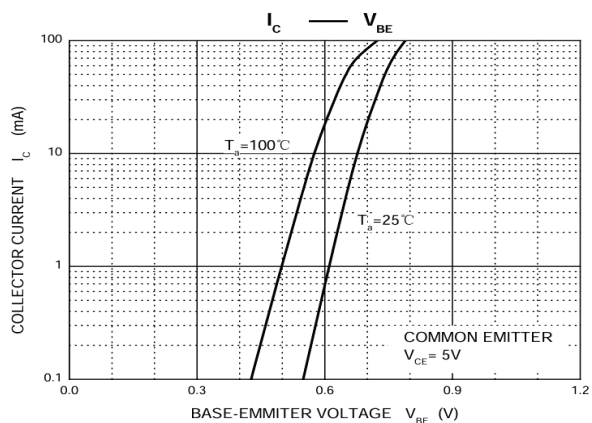
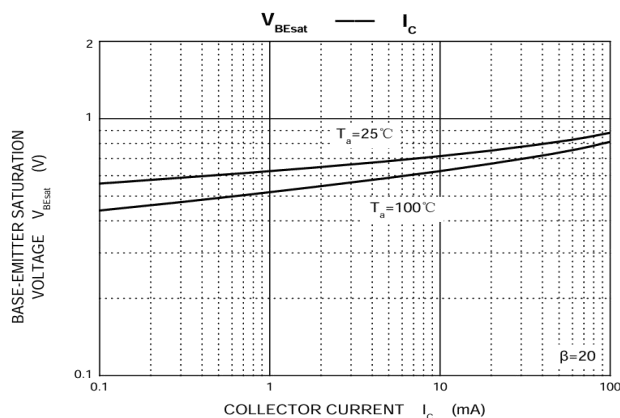
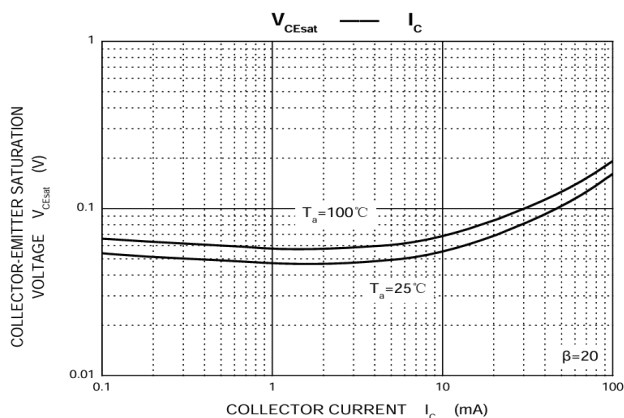
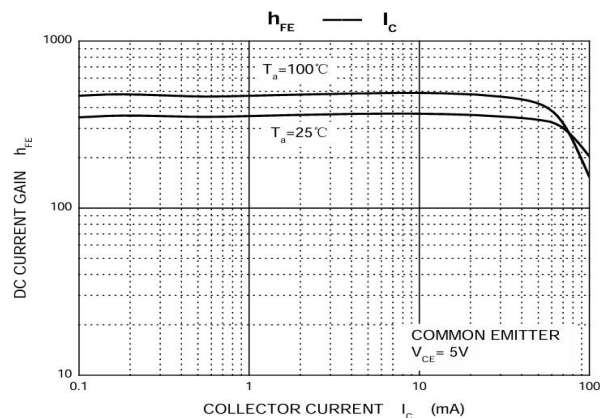
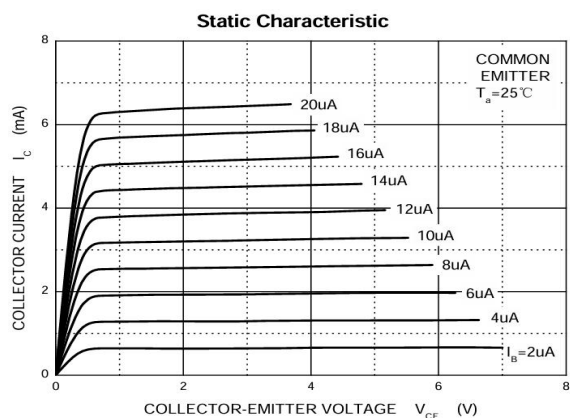
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100μA, I _E =0	50		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	45		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	5		V
Collector cutoff current	I _{CBO}	V _{CB} =50V, I _E =0		0.1	μA
Collector cut-off current	I _{CEO}	V _{CE} =35V, I _B =0		1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =3V, I _C =0		0.1	μA
DC Current Gain (CLASSIFICATION OF hFE)	h _{FE}	V _{CE} =5V, I _C =1mA	60	150	
			100	300	
			200	600	
			400	1000	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =100mA, I _B =5mA		0.3	V
Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C =100mA, I _B =5mA		1	V
Transition frequency	f _T	V _{CE} =5V, I _C =10mA, f=30MHz	150		MHz



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TYPICAL CHARACTERISTICS

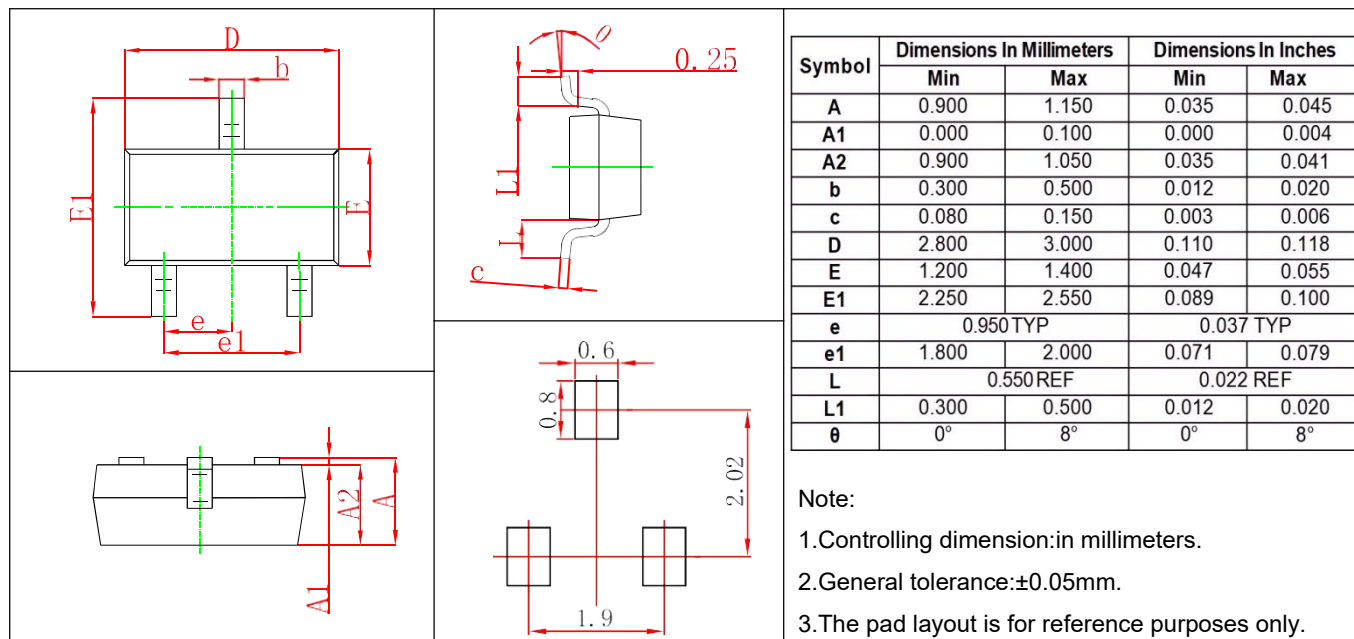




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SOT23 PACKAGE OUTLINE DIMENSIONS



REEL PACKING

